Octal 3-State Noninverting D Flip-Flop with LSTTL-Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT374A may be used as a level converter for interfacing TTL or NMOS outputs to High-Speed CMOS inputs.

The HCT374A is identical in pinout to the LS374.

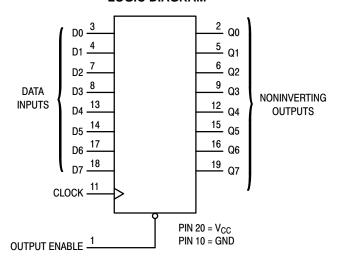
Data meeting the setup and hold time is clocked to the outputs with the rising edge of Clock. The Output Enable does not affect the state of the flip-flops, but when Output Enable is high, the outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

The HCT374A is identical in function to the HCT574A, which has the input pins on the opposite side of the package from the output pins. This device is similar in function to the HCT534A, which has inverting outputs.

Features

- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance With the JEDEC Standard No. 7.0 A Requirements
- Chip Complexity: 276 FETs or 69 Equivalent Gates
- Improvements over HCT374
 - Improved Propagation Delays
 - ◆ 50% Lower Quiescent Power
 - Improved Input Noise and Latchup Immunity
- These Devices are Pb-Free and are RoHS Compliant

LOGIC DIAGRAM





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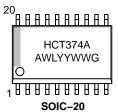


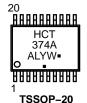
SOIC-20 DW SUFFIX CASE 751D TSSOP-20 DT SUFFIX CASE 948E

PIN ASSIGNMENT

OUTPUT ENABLE	ď	1•	20	þ	V_{CC}
Q0	þ	2	19	þ	Q7
D0	þ	3	18	þ	D7
D1	þ	4	17	þ	D6
Q1	þ	5	16	þ	Q6
Q2	þ	6	15	þ	Q5
D2	þ	7	14	þ	D5
D3	þ	8	13	þ	D4
Q3	þ	9	12	þ	Q4
GND	ď	10	11	þ	CLOCK

MARKING DIAGRAMS





= Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

	Inputs					
Output Enable	Clock	D	Q			
L	_	Н	Н			
L	_	L	L			
L	L,H, ∕ X	Χ	No Change			
Н	Х	Х	Z			

X = don't careZ = high impedance

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

Design Criteria	Value	Units
Internal Gate Count*	69	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рJ

^{*}Equivalent to a two-input NAND gate.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V_{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	±35	mA
Icc	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C TSSOP Package: -6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+125	°C
tr. tr	Input Rise and Fall Time (Figure 1)	0	500	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed	Limit	
Symbol	Parameter	Test Conditions	V _{CC}	–55 to 25°C	≤ 85 °(C ≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	±0.1	±1.0	±1.0	μΑ
l _{OZ}	Maximum Three–State Leakage Current	Output in High–Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	5.5	±0.5	±5.0	±10	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4.0 40 160		μΑ	
ΔI_{CC}	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs		≥ -55°(2	5°C to 125°C	
		$I_{\text{out}} = 0 \mu\text{A}$	5.5	2.9		2.4	mA

^{1.} Total Supply Current = $I_{CC} + \Sigma \Delta I_{CC}$.

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5.0 V $\pm 10\%$, C_L = 50 pF, Input t_f = t_f = 6.0 ns)

		Guaranteed Limit			
Symbol	Parameter	–55 to 25°C	≤ 85 ° C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	30	24	20	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q (Figures 1 and 4)	31	39	47	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	30	38	45	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5)	30	38	45	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	12	15	18	ns
C _{in}	Maximum Input Capacitance	10	10	10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)	15	15	15	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Flip-Flop)*	65	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

TIMING REQUIREMENTS (V_{CC} = 5.0 V \pm 10%, Input t_{r} = t_{f} = 6.0 ns)

		Guaranteed Limit			
Symbol	Parameter	-55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{su}	Minimum Setup Time, Data to Clock (Figure 3)	12	15	18	ns
t _h	Minimum Hold Time, Clock to Data (Figure 3)	5.0	5.0	5.0	ns
t _w	Minimum Pulse Width, Clock (Figure 1)	12	15	18	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	500	500	500	ns

SWITCHING WAVEFORMS

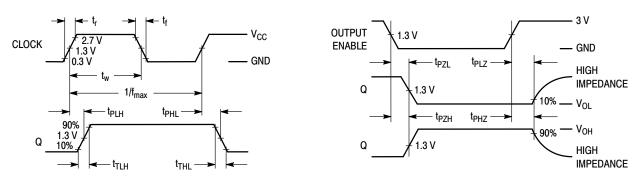


Figure 1.

Figure 2.

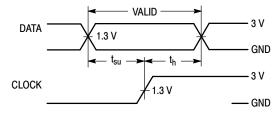
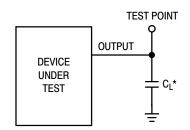


Figure 3.

TEST CIRCUITS



^{*}Includes all probe and jig capacitance

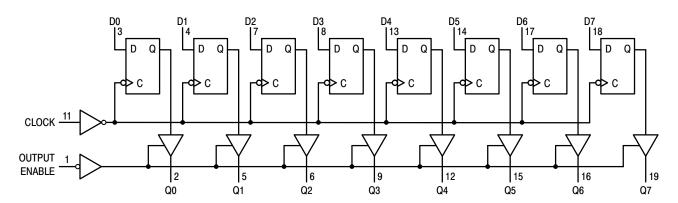
 $\begin{array}{c|c} & \text{TEST POINT} \\ & \text{OUTPUT} & \text{OUTPUT} & \text{CONNECT TO V_{CC} WHEN } \\ & \text{DEVICE} & \text{UNDER } \\ & \text{UNDER } & \text{TEST} \\ & \text{TEST} & \\ & & \text{C}_{L}^{\star} & \\ \end{array}$

*Includes all probe and jig capacitance

Figure 5.

Figure 4.

EXPANDED LOGIC DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT374ADWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74HCT374ADWR2G	SOIC-20 (Pb-Free)	1000 Units / Reel
MC74HCT374ADTR2G	TSSOP-20 (Pb-Free)	2500 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
b	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
A	0 °	7 °		

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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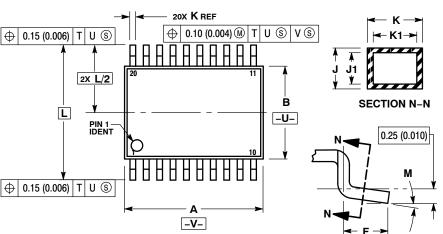
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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016





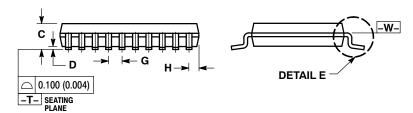
DETAIL E

NOTES:

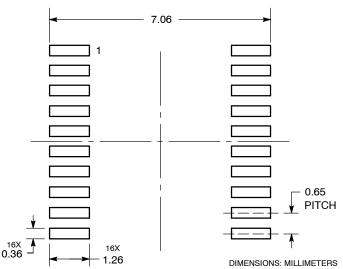
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

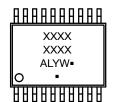
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°



SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot = Year

= Work Week

= Pb-Free Package (Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■",

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